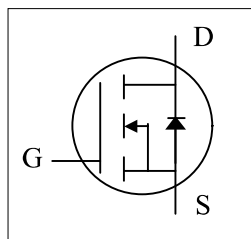


N-Channel Power MOSFET

- ▼ Capable of 2.5V Gate Drive
- ▼ Small Size & Ultra_Low $R_{DS(ON)}$
- ▼ RoHS Compliant & Halogen-Free



BV_{DSS}	20V
$R_{DS(ON)}$	8.5m Ω
I_D^3	30A

Description

AP2080Q series are from Advanced Power innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.



DFN3 x 3

Absolute Maximum Ratings@ $T_J=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D@T_A=25^\circ\text{C}$	Drain Current, $V_{GS} @ 4.5V^3$	30	A
$I_D@T_A=70^\circ\text{C}$	Drain Current, $V_{GS} @ 4.5V^3$	19	A
I_{DM}	Pulsed Drain Current ¹	70	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation	24	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Value	Unit
R_{thj-c}	Maximum Thermal Resistance, Junction-case	5	$^\circ\text{C}/\text{W}$
R_{thj-a}	Maximum Thermal Resistance, Junction-ambient ³	26	$^\circ\text{C}/\text{W}$

N-Channel Power MOSFET

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	20	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =4.5V, I _D =20A	-	8.5	9.8	mΩ
		V _{GS} =2.5V, I _F =12A	-	-	14	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =1mA	0.6	-	0.9	V
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =20A	-	130	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =16V, V _{GS} =0V	-	-	10	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±12V, V _{DS} =0V	-	-	±100	nA
Q _g	Total Gate Charge	I _D =20A	-	62	99.2	nC
Q _{gs}	Gate-Source Charge	V _{DS} =10V	-	4	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =4.5V	-	21	-	nC
t _{d(on)}	Turn-on Delay Time	V _{DS} =10V	-	12	-	ns
t _r	Rise Time	I _D =1A	-	20	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω	-	100	-	ns
t _f	Fall Time	V _{GS} =5V	-	80	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	4000	6400	pF
C _{oss}	Output Capacitance	V _{DS} =10V	-	780	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	625	-	pF
R _g	Gate Resistance	f=1.0MHz	-	1.4	2.8	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =2.5A, V _{GS} =0V	-	-	1.2	V
t _{rr}	Reverse Recovery Time	I _S =20A, V _{GS} =0V,	-	43	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	26	-	nC

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted on 1 in² 2oz copper pad of FR4 board, t ≤10sec; 135°C/W when mounted on min. copper pad.
- 4.Maximum current limited by package.

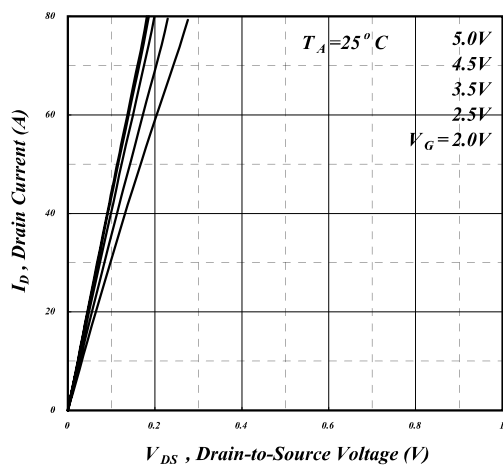


Fig 1. Typical Output Characteristics

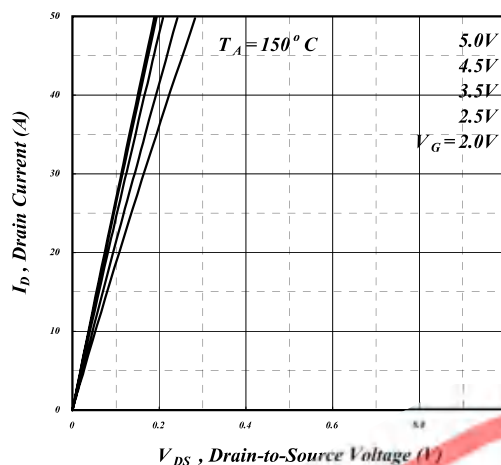


Fig 2. Typical Output Characteristics

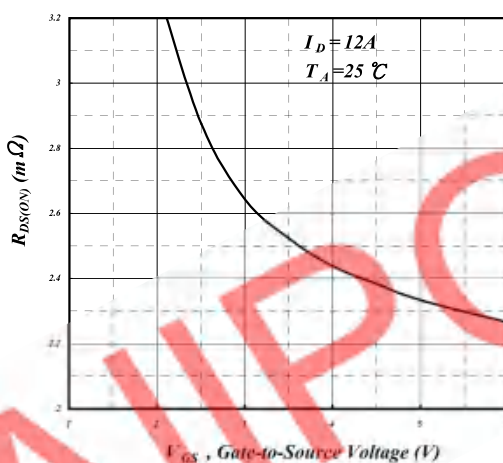


Fig 3. On-Resistance v.s. Gate Voltage

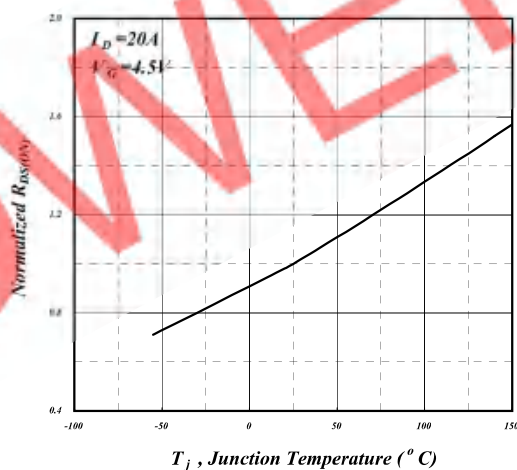


Fig 4. Normalized On-Resistance v.s. Junction Temperature

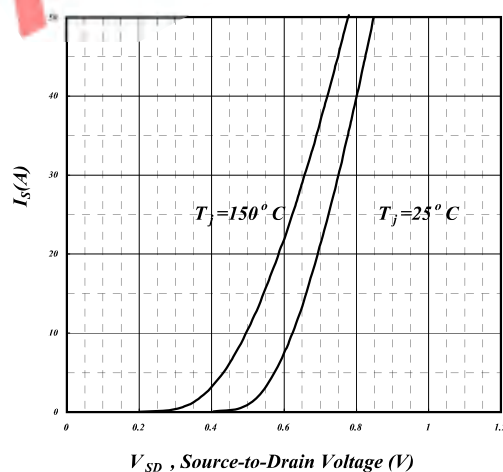


Fig 5. Forward Characteristic of Reverse Diode

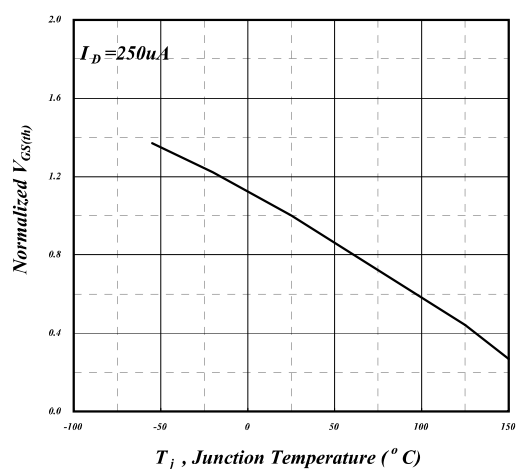
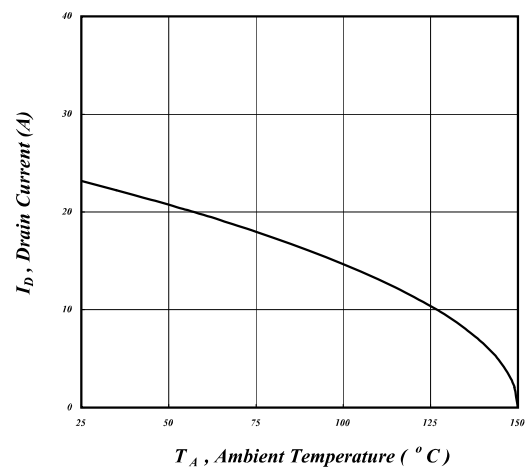
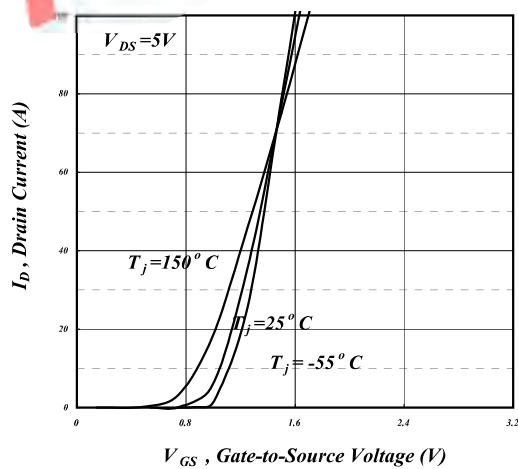
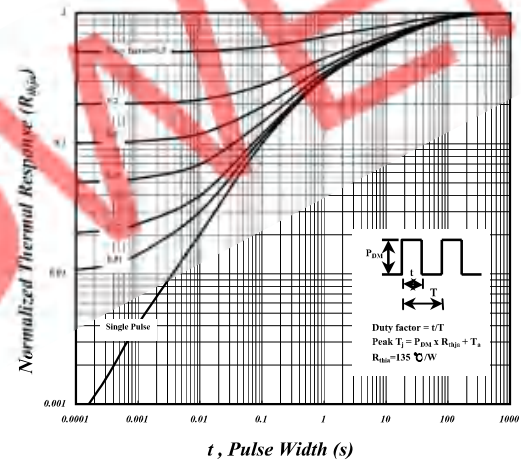
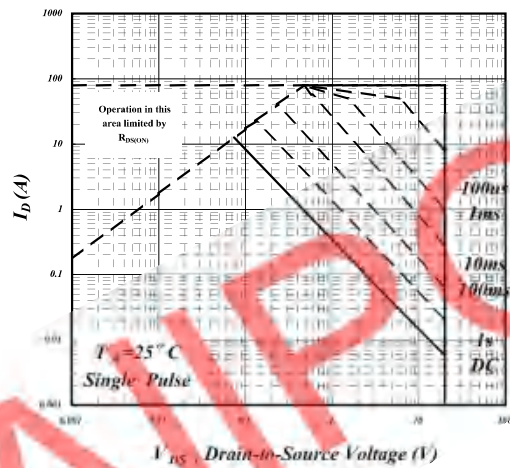
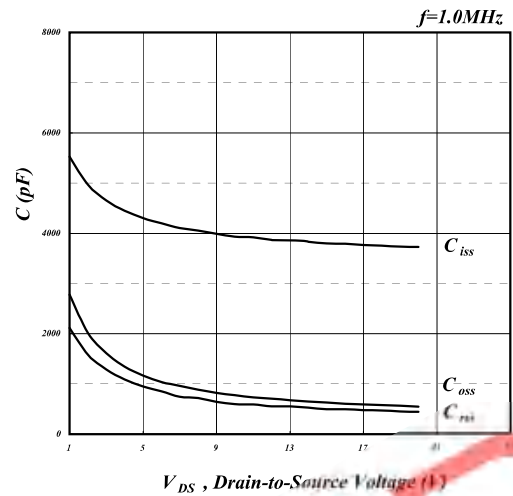
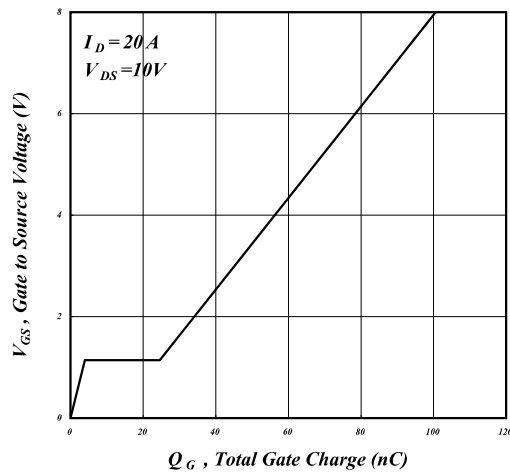


Fig 6. Gate Threshold Voltage v.s. Junction Temperature



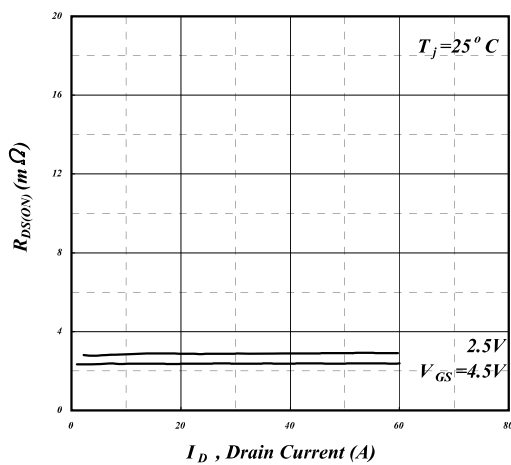


Fig 13. Typ. Drain-Source on State Resistance

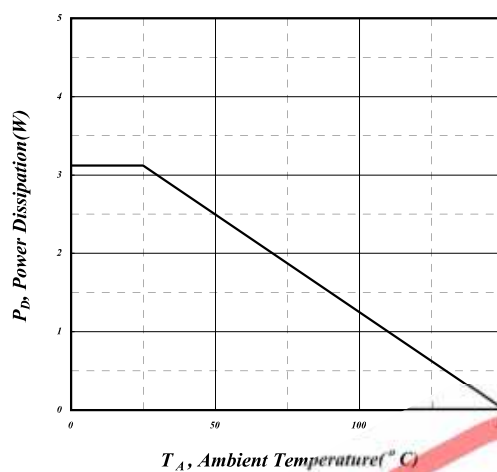
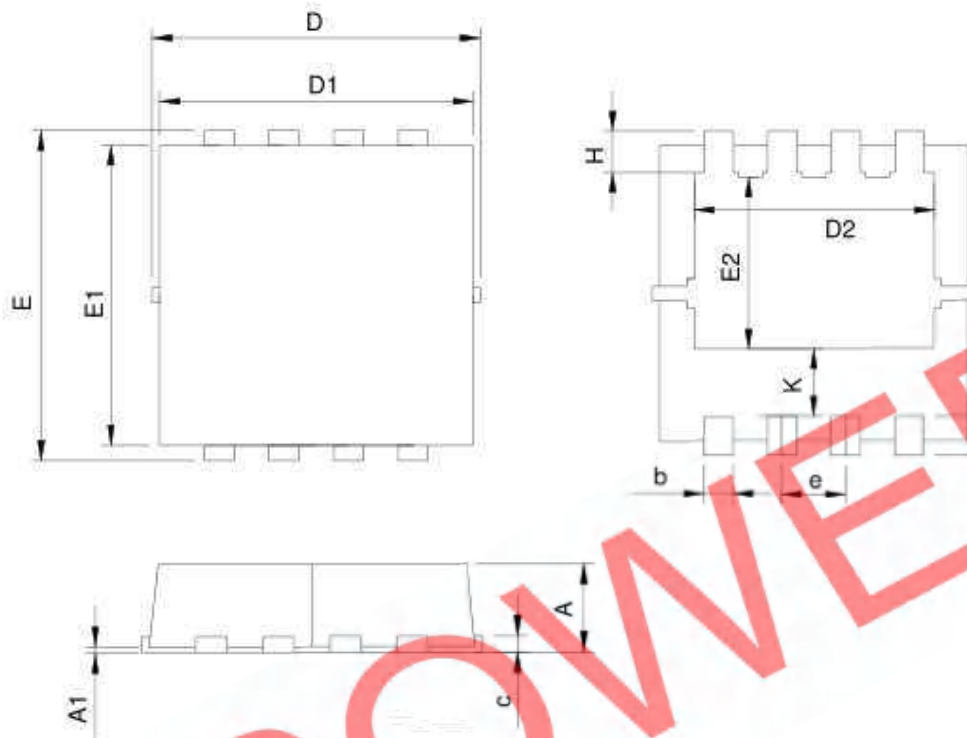


Fig 14. Total Power Dissipation

N-Channel Power MOSFET

●Dimensions(DFN3×3)



	DFN3.3x3.3-8			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.70	1.00	0.028	0.039
A1	0.00	0.05	0.000	0.002
b	0.25	0.35	0.010	0.014
c	0.14	0.20	0.006	0.008
D	3.10	3.50	0.122	0.138
D1	3.05	3.25	0.120	0.128
D2	2.35	2.55	0.093	0.100
E	3.10	3.50	0.122	0.138
E1	2.90	3.10	0.114	0.122
E2	1.64	1.84	0.065	0.072
e	0.65 BSC		0.026 BSC	
H	0.32	0.52	0.013	0.020
K	0.59	0.79	0.023	0.031
L	0.25	0.55	0.010	0.022

RECOMMENDED LAND PATTERN

